

**Schottky Barrier Rectifier**  
**Reverse Voltage 40 to 200 Volts**  
**Forward Current 30 Amperes**

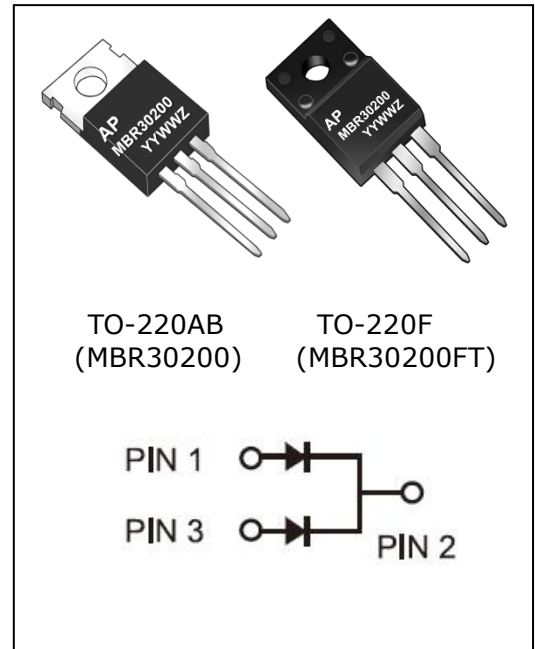
**Features**

- Metal silicon junction majority carrier conduction
- Guard ring for overvoltage protection
- Low power loss, high efficiency
- High current capability, low forward voltage drop
- High surge capability
- High temperature soldering guaranteed:  
260°C/10 seconds at terminals
- Plastic package has Underwriters Laboratory  
Flammability Classification 94V-0
- For use in low voltage, high frequency inverters,  
free-wheeling, and polarity protection application

**Technical Data**

**Case :** JEDEC ITO-220AB molded plastic body

**Terminals :** Plated axial leads, solderable  
per MIL-STD-750, method 2026



**Maximum Ratings Characteristics**

TA = 25°C unless otherwise specified.

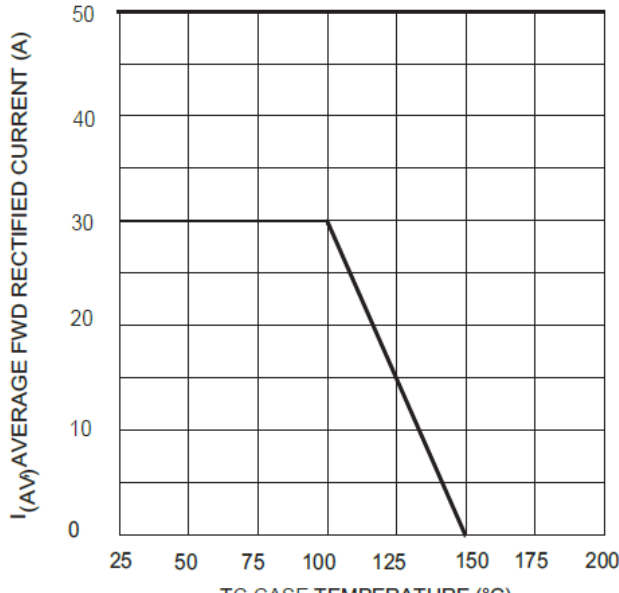
Parameter	Symbol	MBR 3040	MBR 3045	MBR 3060	MBR 3080	MBR 30100	MBR 30120	MBR 30150	MBR 30200	Unit
Maximum Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	40	50	60	80	100	120	150	200	V
Maximum RMS voltage	V <sub>RMS</sub>	28	31.5	42	56	70	84	105	140	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	40	45	60	80	100	120	150	200	V
Maximum Average Forward Rectified Current 0.375" (9.5mm) lead length	I <sub>F(AV)</sub>	30.0								A
Peak forward surge current, 8.3mS single half sine-wave superimposed on rated load	I <sub>FSM</sub>	200.0								A
Maximum instantaneous forward voltage at 1/2I <sub>F(AV)</sub>	V <sub>F</sub>	0.55		0.75		0.85		0.90	0.95	V
Maximum DC Reverse Current at Rated DC Blocking Voltage	T <sub>a</sub> = 25°C	0.5			0.1				mA	
	T <sub>a</sub> = 100°C	50			10					
Typical Junction Capacitance <sup>(1)</sup>	C <sub>j</sub>	260								pF
Typical Thermal Resistance <sup>(2)</sup>	R <sub>θJC</sub>	4								°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150								°C

**Note**

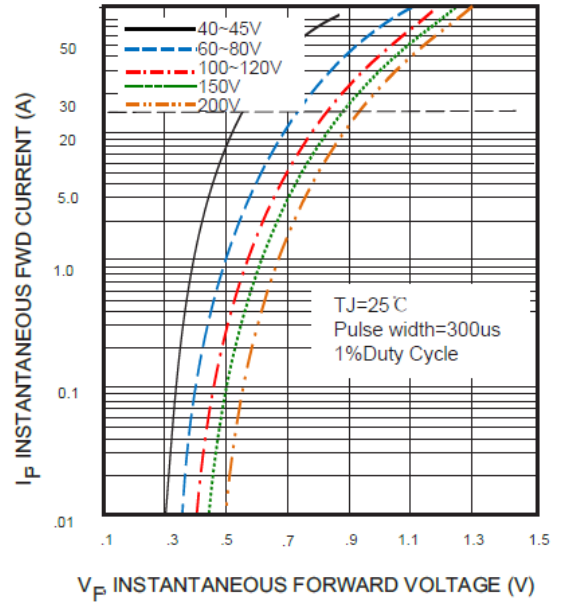
- (1) Single phase, half wave, 60HZ, resistive or inductive load. For capacitive load, derate current by 20%.
- (2) PCB mounted with 0.2X0.2"(5.0X5.0 mm) copper pad areas.

**Characteristics Curves**

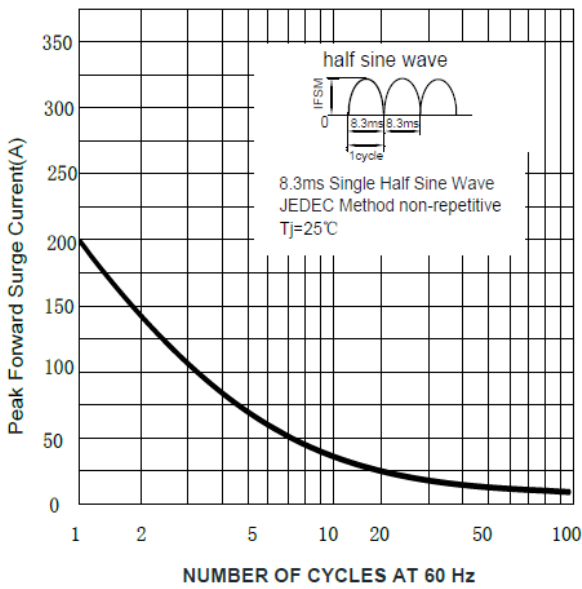
( TA = 25°C unless otherwise specified )



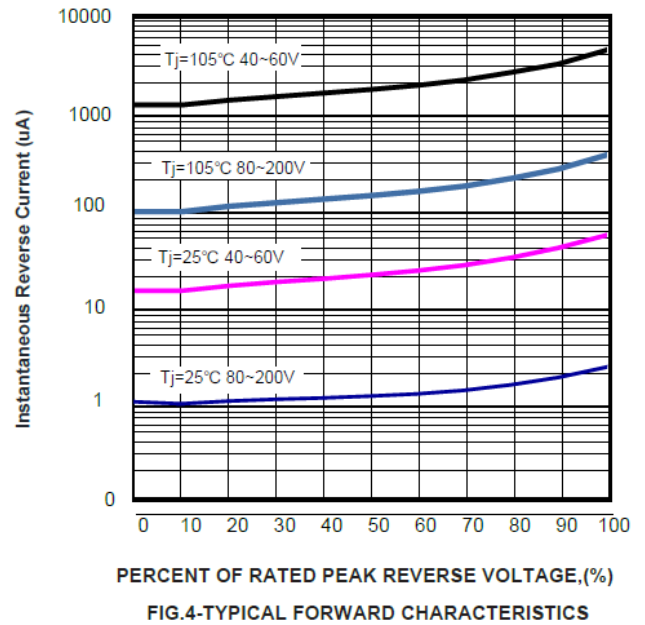
TC, CASE TEMPERATURE (°C)  
Fig. 1 Forward Derating Curve



$V_F$  INSTANTANEOUS FORWARD VOLTAGE (V)  
Fig. 2 Typical Forward Characteristics



NUMBER OF CYCLES AT 60 Hz  
Fig. 3 Peak Forward Surge Current



PERCENT OF RATED PEAK REVERSE VOLTAGE.(%)  
FIG.4-TYPICAL FORWARD CHARACTERISTICS

**Revision History**

REV. 00



No	Date	Contents
0	2018-06-08	Initial Brief Datasheet Release

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### IMPORTANT NOTICE

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